

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	532	@ad<="20030915" and ('memory' or 'DRAM' or 'SRAM') and ('peripheral' or logic) and 'dual' with 'polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 08:19
L4	35	@ad<="20030915" and ('memory' or 'DRAM' or 'SRAM') and ('peripheral' or logic) and 'dual' with 'doped polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 08:36
L5	1076	@ad<="20030915" and 'SRAM' and ('peripheral' or logic) and 'doped polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 08:36
L6	841	@ad<="20030915" and 'SRAM' and 'logic' and 'doped polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 08:42
L7	2	@ad<="20030915" and 'SRAM' and 'logic' and 'dual' with 'doped' with 'polysilicon gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 08:43
L9	79	@ad<="20030915" and 'memory' and 'logic' and 'dual' with 'polysilicon gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 08:58
L10	1027	@ad<="20030915" and 'memory' and 'logic' and 'first polysilicon' and 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 08:59
L11	230	@ad<="20030915" and 'SRAM' and 'logic' and 'first polysilicon' and 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 08:59
L12	1	"6506647".PN.	USPAT; USOCR	OR	ON	2005/12/28 09:07
L13	640	@ad<="20030915" and (438/241).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:54
L14	1035	@ad<="20030915" and (438/238).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:20

L15	810	@ad<="20030915" and (257/e21.661).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 11:31
L16	828	@ad<="20030915" and (257/903).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:23
L17	642	@ad<="20030915" and (257/e27.098).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:24
L18	332	@ad<="20030915" and (365/185.08).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:24
L19	298	@ad<="20030915" and (438/210).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:54
L20	61	('cell' and 'peripheral' and ('first' with 'polysilicon') and ('second' with 'polysilicon') and 'gate oxide').clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 11:34
S1	9	@ad<="20030915" and 'cell' same 'logic' same 'cell gate oxide' and 'polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 15:42
S2	30	@ad<="20030915" and 'SRAM' same 'dual' with 'polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 15:53
S3	6963	@ad<="20030915" and (257/382).ccls. or (257/532).ccls. or (257/755).ccls. or (257/763).ccls. or (257/E21.507).ccls. or (257/E21.59).ccls. or (257/E21.593).ccls. or (257/E21.66).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 14:41
S4	3125	@ad<="20030915" and (438/238).ccls. or (438/586).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 14:41
S5	1	"6080647".PN.	USPAT; USOCR	OR	ON	2004/12/06 16:19
S6	1	"5866451".PN.	USPAT; USOCR	OR	ON	2004/12/06 16:19

S7	5938	@ad<="20030915" and (438/621). ccls. or (438/655).ccls. or (438/656).ccls. or (438/657).ccls. or (438/253).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:29
S8	1	"6294420".PN.	USPAT; USOCR	OR	ON	2004/12/06 16:22
S9	1	"6177340".PN.	USPAT; USOCR	OR	ON	2004/12/06 16:22
S10	2030	@ad<="20030915" and (438/585). ccls. or (438/152).ccls. or (438/594).ccls. or (438/734).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 16:29
S12	159	@ad<="20030915" and 'SRAM' same 'polysilicon layers' and 'cell' and 'logic'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 17:21
S13	122	@ad<="20030915" and 'SRAM' same 'polysilicon layers' and 'cell' and 'peripheral'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 14:42
S14	2188	@ad<="20030915" and (438/253). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 17:03
S15	174	@ad<="20030915" and 'SRAM' same 'first polysilicon' and 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 07:07
S16	669	@ad<="20030915" and 'SRAM' and 'first polysilicon' and 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 17:22
S17	543	@ad<="20030915" and 'SRAM' and 'first polysilicon' and 'second polysilicon' and 'cell' and 'device'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/06 17:23
S18	304	@ad<="20030915" and 'SRAM' and 'first polysilicon' and 'second polysilicon' and 'cell' same 'device' same 'region'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 08:28
S19	653	@ad<="20030915" and 'SRAM' same 'memory' and 'peripheral' and 'polysilicon layers'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 08:29

S20	301	@ad<="20030915" and 'SRAM' and 'first polysilicon' and 'second polysilicon' and 'memory' same 'device' same 'region'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 08:29
S21	9	@ad<="20030915" and 'SRAM' same 'memory' same 'peripheral' same 'polysilicon layers'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 08:29
S22	811	@ad<="20030915" and (257/903).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:23
S23	324	@ad<="20030915" and (257/380-381).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:40
S24	138	@ad<="20030915" and (257/385).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:41
S25	260	@ad<="20030915" and (257/756).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:41
S26	501	@ad<="20030915" and (438/647).ccls. or (438/657).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:43
S27	196	@ad<="20030915" and (438/630).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/07 12:45
S28	7129	@ad<="20030915" and (257/382).ccls. or (257/532).ccls. or (257/755).ccls. or (257/763).ccls. or (257/E21.507).ccls. or (257/E21.59).ccls. or (257/E21.593).ccls. or (257/E21.66).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 14:41
S29	3176	@ad<="20030915" and (438/238).ccls. or (438/586).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 10:12
S30	123	@ad<="20030915" and 'SRAM' same 'polysilicon layers' and 'cell' and 'peripheral'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 14:43

S31	123	@ad<="20030915" and 'SRAM' same 'polysilicon layers' and 'cell' and 'peripheral'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 09:39
S32	10	@ad<="20030915" and 'cell' same 'logic' same 'cell gate oxide' and 'polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 15:42
S35	0	@ad<="20030915" and 'cell' with 'gate oxide' and 'logic' with 'gate oxide' and 'doped polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 15:56
S36	726	@ad<="20030915" and 'cell' with 'oxide' and 'logic' with 'oxide' and 'polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 15:57
S37	215	@ad<="20030915" and 'cell' with 'oxide' and 'logic' with 'oxide' and 'doped polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 15:57
S38	179	'SRAM' same 'first polysilicon' and 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 08:05
S39	720	'SRAM' and 'first polysilicon' and 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 07:08
S40	1163	'memory' and 'peripheral' and 'first polysilicon' and 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 08:06
S41	1129	'memory' and 'logic' and 'first polysilicon' and 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 08:23
S42	19	'memory' with 'dual gate' and 'logic' and 'first polysilicon' and 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 08:21
S43	1	"5155056".PN.	USPAT; USOCR	OR	ON	2005/09/02 08:17
S44	1	"5395784".PN.	USPAT; USOCR	OR	ON	2005/09/02 08:18

S45	684	'memory' same 'logic' and 'first polysilicon' same 'second polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 08:23
S46	78	@ad<="20030915" and 'memory' and 'logic' and 'dual' with 'polysilicon gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 09:31
S47	1	"5656839".PN.	USPAT; USOCR	OR	ON	2005/09/02 09:33
S48	1	"5736421".PN.	USPAT; USOCR	OR	ON	2005/09/02 09:33
S49	1	"20030062566".PN.	US-PGPUB	OR	ON	2005/09/02 09:34
S50	162	@ad<="20030915" and 'SRAM' same 'polysilicon layers' and 'cell' and 'logic'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 09:40
S51	19	@ad<="20030915" and 'SRAM' same 'dual' same 'polysilicon' and 'logic'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 09:41
S52	7	@ad<="20030915" and 'SRAM' same 'dual' same 'polysilicon' and 'peripheral'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 09:41
S53	5	@ad<="20030915" and 'SRAM' with 'dual' same 'polysilicon' and 'peripheral'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 09:51
S54	1	@ad<="20030915" and 'SRAM' and 'logic gate' and 'cell gate' same 'doped polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 09:52
S55	122	@ad<="20030915" and 'SRAM' and 'logic gate' and 'cell gate'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 09:53
S56	0	@ad<="20030915" and 'SRAM' and 'logic gate' and 'cell gate' with 'dual' with 'polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 09:53
S57	437	@ad<="20030915" and 'memory' same 'gate' same 'dual' same 'polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 09:54

S58	194	@ad<="20030915" and 'memory' with 'gate' same 'dual' with 'polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 09:55
S59	1	"6432768".PN.	USPAT; USOCR	OR	ON	2005/09/02 10:03
S60	1	"6391704".PN.	USPAT; USOCR	OR	ON	2005/09/02 10:05
S61	1	"6218715".PN.	USPAT; USOCR	OR	ON	2005/09/02 10:06
S62	1	"6218715".PN.	USPAT; USOCR	OR	ON	2005/09/02 10:06
S63	1	"6168984".PN.	USPAT; USOCR	OR	ON	2005/09/02 10:07
S64	1	"6096595".PN.	USPAT; USOCR	OR	ON	2005/09/02 10:07
S65	1	"6015730".PN.	USPAT; USOCR	OR	ON	2005/09/02 10:11
S66	1	"5998252".PN.	USPAT; USOCR	OR	ON	2005/09/02 10:11
S67	1	"5863820".PN.	USPAT; USOCR	OR	ON	2005/09/02 10:12
S69	1921	@ad<="20030915" and (438/257). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 10:13
S70	634	@ad<="20030915" and (438/241). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/28 10:20
S71	232	@ad<="20030915" and (438/157). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 10:17
S72	282	@ad<="20030915" and (438/152). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 10:17